

Silicon PNP Power Transistors

2SB649 2SB649A

DESCRIPTION

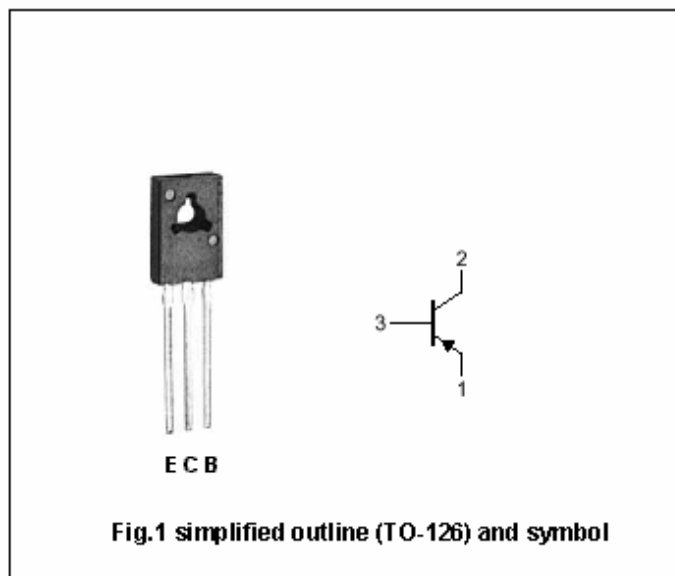
- With TO-126 package
- Complement to type 2SD669/669A
- High breakdown voltage V_{CEO} : -120/-160V
- High current -1.5A
- Low saturation voltage, excellent h_{FE} linearity

APPLICATIONS

- For low-frequency power amplifier applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector; connected to mounting base
3	Base

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SB649	Open emitter	-180	V
		2SB649A		-180	
V_{CEO}	Collector-emitter voltage	2SB649	Open base	-120	V
		2SB649A		-160	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current (DC)			-1.5	A
I_{CM}	Collector current-Peak			-3	A
P_D	Total power dissipation		$T_a=25^\circ\text{C}$	1	W
			$T_c=25^\circ\text{C}$	20	
T_j	Junction temperature			150	$^\circ\text{C}$
T_{stg}	Storage temperature			-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SB649	$I_C = -10mA; R_{BE} = \infty$	-120			V
		2SB649A		-160			
$V_{(BR)CBO}$	Collector-base breakdown voltage	2SB649	$I_C = -1mA; I_E = 0$	-180			V
		2SB649A		-180			
$V_{(BR)EBO}$	Emitter-base breakdown voltage		$I_E = -1mA; I_C = 0$	-5			V
V_{CEsat}	Collector-emitter saturation voltage		$I_C = -0.5A; I_B = -50mA$			-1.0	V
V_{BE}	Base-emitter voltage		$I_C = -150mA; V_{CE} = 5V$			-1.5	V
I_{CBO}	Collector cut-off current		$V_{CB} = -160V; I_E = 0$			-10	μA
h_{FE-1}	DC current gain	2SB649	$I_C = -150mA; V_{CE} = -5V$	60		320	
		2SB649A		60		200	
h_{FE-2}	DC current gain		$I_C = -0.5A; V_{CE} = -5V$	30			
f_T	Transition frequency		$I_C = -150mA; V_{CE} = -5V$		140		MHz
C_{OB}	Collector output capacitance		$f = 1MHz; V_{CB} = -10V$		27		pF

◆ h_{FE} Classifications

h_{FE-1}	B	C	D
2SB649	60-120	100-200	160-320
2SB649A	60-120	100-200	

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PACKAGE OUTLINE

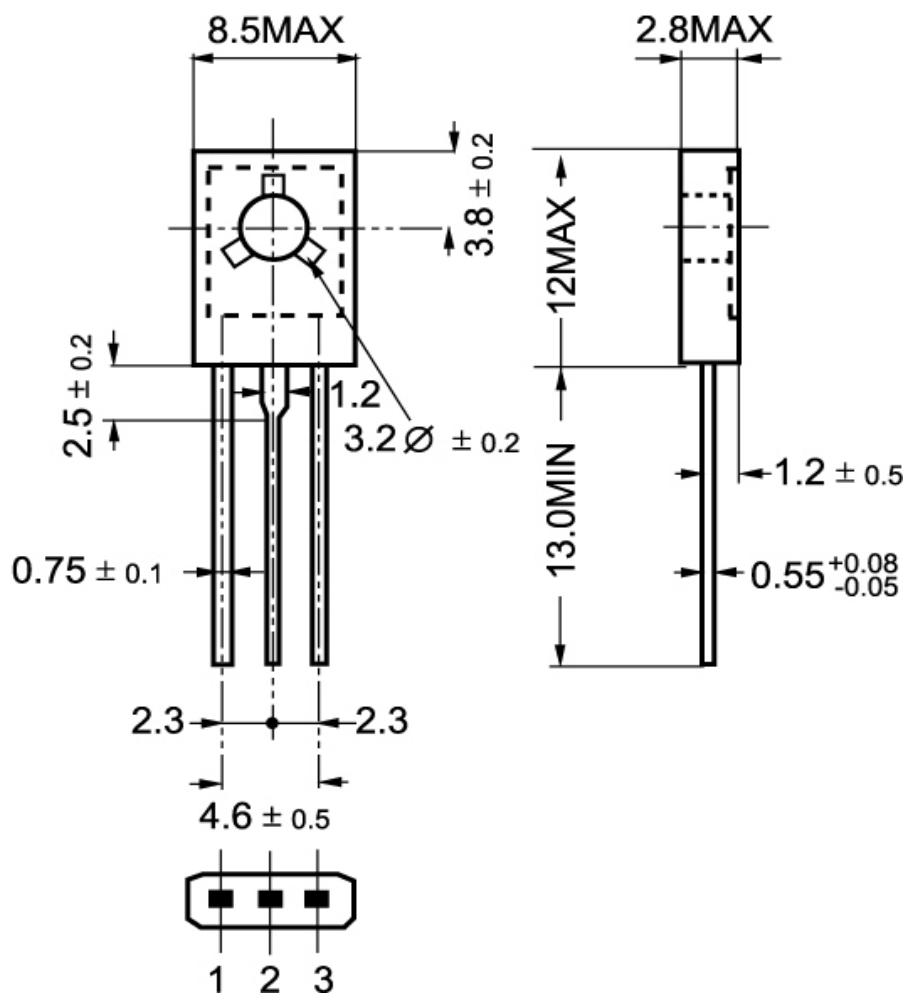


Fig.2 Outline dimensions

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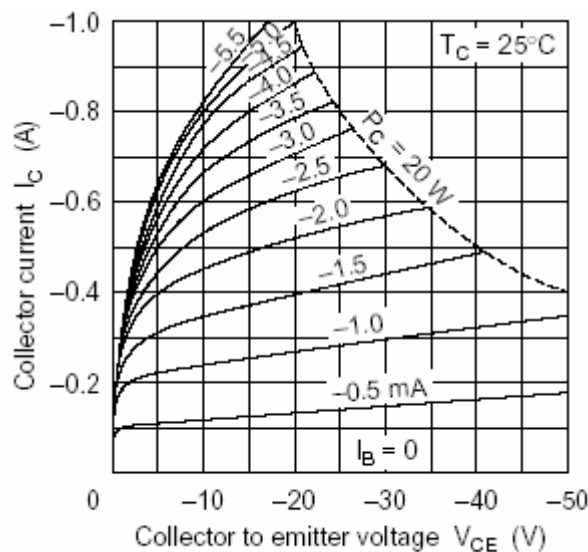


Fig.3 Static Characteristic

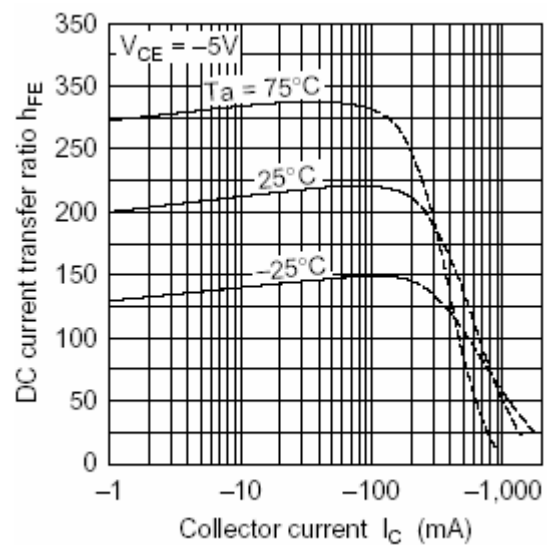


Fig.4 DC current Gain

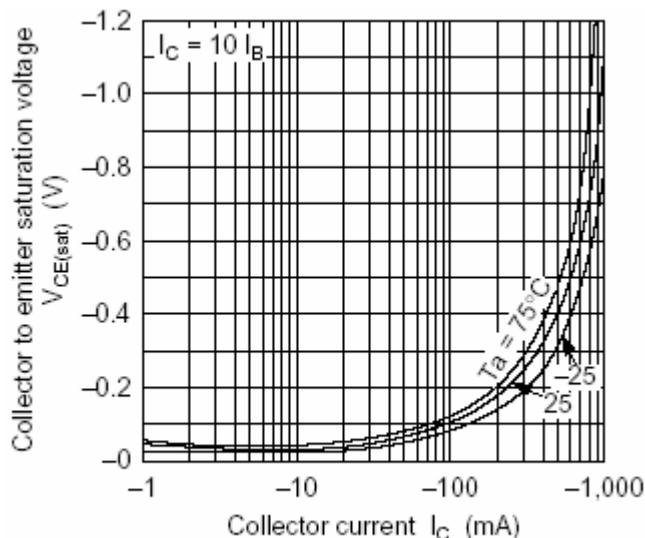


Fig.5 Collector-Emitter Saturation Voltage

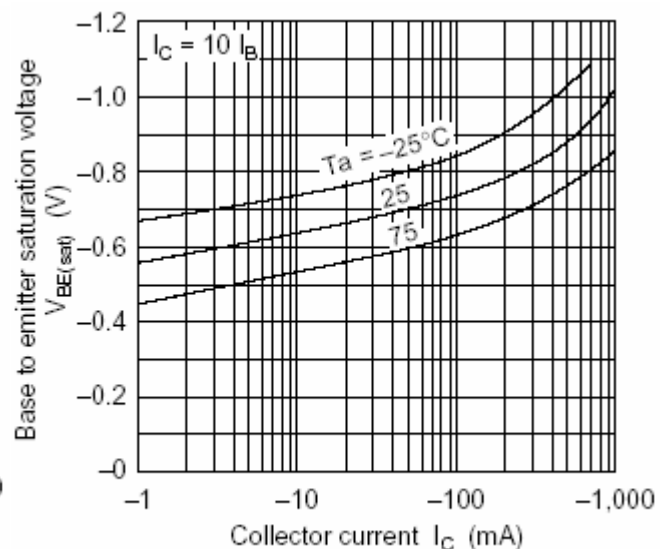


Fig.6 Base-Emitter Saturation Voltage

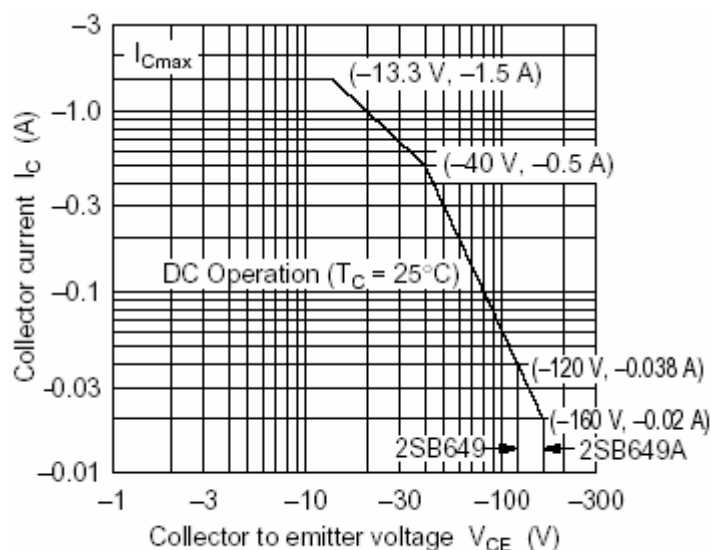


Fig.7 Safe Operating Area